

## **IN THE CLAIMS**

Please cancel claims 1-11 without prejudice.

1.-11. (Canceled)

12. (Original) An apparatus, comprising:

an indium-fluorine retrograde well inside a substrate, the indium-fluorine retrograde well including an indium concentration greater than about  $3E18/cm^3$ .

13. (Original) The apparatus of claim 12, wherein the indium-fluorine retrograde well includes an indium concentration three times, or more, greater than  $3E18/cm^3$ .

14. (Original) The apparatus of claim 12, wherein the indium-fluorine retrograde well includes a fluorine concentration between about  $5E18/cm^3$  to about  $3E20/cm^3$ .

15. (Original) The apparatus of claim 12, wherein the indium-fluorine retrograde well includes an indium concentration peak at about  $200\text{\AA}$ , or deeper, below the substrate surface.

16. (Original) An integrated circuit, comprising:

a substrate;

a gate structure formed on the substrate; and

an indium-fluorine retrograde well formed to a shallow depth below a surface of the substrate and beneath the gate structure.

17. (Original) The integrated circuit of claim 16, comprising an indium concentration above about  $3 \times 10^{18}$ .

18. (Original) The apparatus of claim 16, wherein the indium-fluorine retrograde well includes an indium concentration three times, or more, greater than  $3 \times 10^{18}/\text{cm}^3$ .

19. (Original) The apparatus of claim 16, wherein the indium-fluorine retrograde well includes a fluorine concentration between about  $5 \times 10^{18}/\text{cm}^3$  to about  $3 \times 10^{20}/\text{cm}^3$ .

20. (Original) The integrated circuit of claim 16, wherein the indium has a concentration peak at about  $200 \text{ \AA}$ , or deeper, below the substrate surface.

21. (Original) An apparatus, comprising:

a gate structure overlying a silicon substrate;

source/drain regions inside the silicon substrate, the source/drain regions adjacent to opposing sides of the gate structure and extending slightly underneath the gate structure; and

a fluorine-indium retrograde well directly beneath the gate structure and between the source/drain regions, the fluorine-indium retrograde well including an indium concentration greater than  $3 \times 10^{18}/\text{cm}^3$ .

22. (Original) The apparatus of claim 21, wherein the fluorine-indium retrograde well is to provide a threshold voltage greater than about  $360 \text{ mV}$ .

23. (Original) The apparatus of claim 21, wherein the fluorine-indium retrograde well includes an indium concentration peak at about 200Å, or deeper, below the substrate surface.
24. (Original) The apparatus of claim 21, wherein the gate structure has a gate length of about 60nm or less.
25. (Original) The apparatus of claim 21, wherein the fluorine-indium retrograde well includes an indium concentration three times, or more, greater than  $3 \times 10^{18}/\text{cm}^3$ .

If there are any additional charges, please charge Deposit Account No. 02-2666.

Respectfully submitted,

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